Product data sheet

1. General description

Planar passivated high commutation triac in a SOT223 surface mounted plastic package. This "series E" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers.

2. Features and benefits

- · 3Q technology for improved noise immunity
- Direct triggering from low power drivers and logic ICs
- High commutation capability with sensitive gate
- · High immunity to false turn-on by dV/dt
- High voltage capability
- · Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- · Surface mountable package
- · Triggering in three quadrants only

3. Applications

- · General purpose motor control
- Small loads in washing machines
- Solenoid drivers

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage			-	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 106 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3		-	-	1	А
Ітѕм	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$		-	-	13.7	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5		-	-	12.5	Α
Tj	junction temperature			-	-	125	°C
Static characteristics							
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 9$		1	-	10	mA

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 9</u>	1	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 9</u>	1	-	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 11</u>	-	-	12	mA
V_{T}	on-state voltage	I _T = 1.4 A; T _j = 25 °C; <u>Fig. 12</u>	-	1.3	1.5	V
Dynamic ch	naracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 14	600	-	-	V/µs
dI _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 1 A; dV_{com}/dt = 20 V/s; (snubberless condition); gate open circuit	2.5	-	-	A/ms
		V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 1 A; dV_{com}/dt = 10 V/s; gate open circuit	3.5	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	4	T2
2	T2	main terminal 2		G sym051
3	G	gate		symosi
4	T2	main terminal 2	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing guantity		Package issue date
BTA201W-800E		BTA201W-800E ,115	Reel	1000	SOT223	16-Mar-2006

Type number	Marking codes			
	Assembly factory: d	Assembly factory: L		
BTA201W-800E	Jdxxx 8E BTA201	JLxxx 8E BTA201		

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 106 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	1	Α
I _{TSM}	non-repetitive peak on-	full sine wave; T _{j(init)} = 25 °C; t _p = 16.7 ms	-	13.7	Α
	state current	full sine wave; $T_{J(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	-	12.5	Α
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	0.78	A²s
dl _T /dt	rate of rise of on-state current	I _G = 0.2 A	-	100	A/µs
I _{GM}	peak gate current		-	1	Α
P_{GM}	peak gate power		-	2	W
P _{G(AV)}	average gate power	over any 20ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

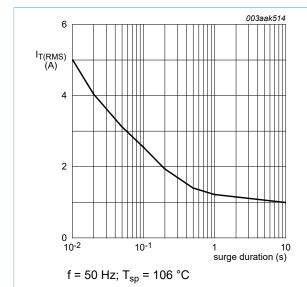


Fig. 1. RMS on-state current as a function of surge duration; maximum values

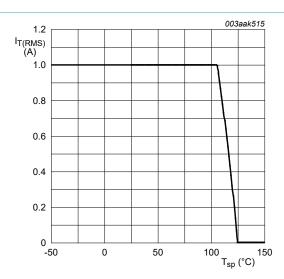


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values

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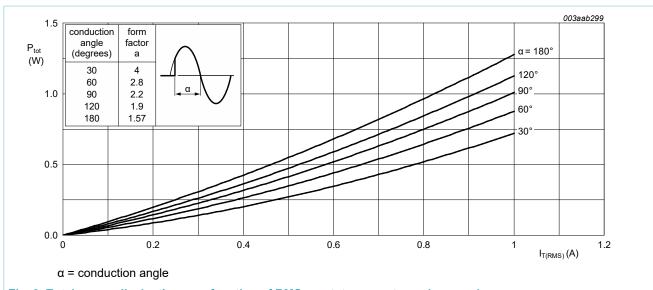


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

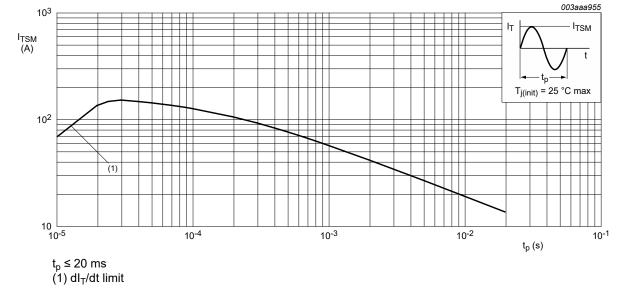


Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

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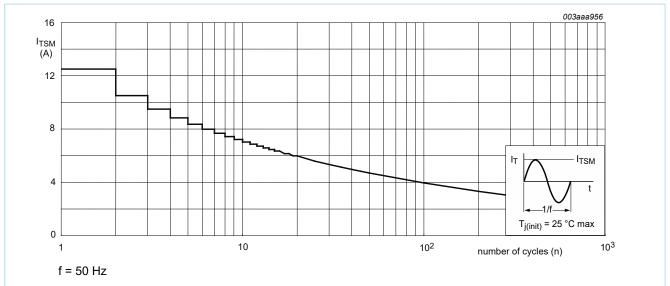
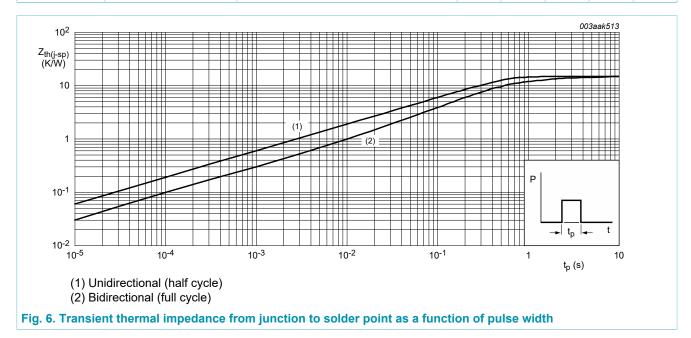


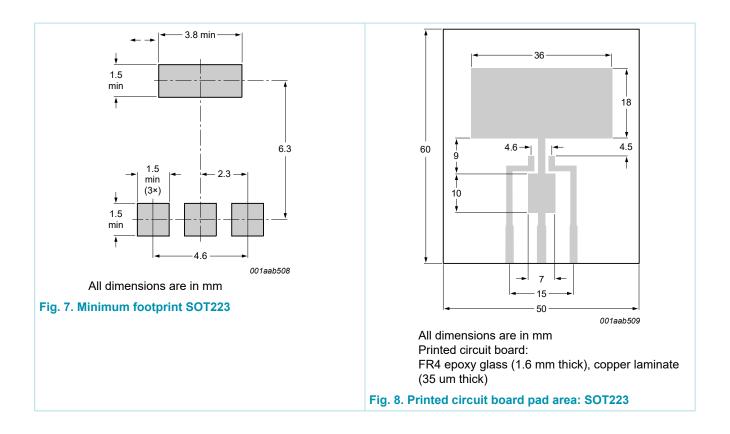
Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	full and half cycle; Fig. 6	-	-	15	K/W
$R_{th(j-a)}$	thermal resistance from junction to	in free air; printed circuit board mounted; minimum footprint; Fig. 7	-	156	-	K/W
	ambient free air	in free air; printed circuit board mounted; pad area; Fig. 8	-	70	-	K/W





9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 9$	1	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 9$	1	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; Fig. 9$	1	-	10	mA
I _L la	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 10$	-	-	12	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 10$	-	-	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. } 10$	-	-	12	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 11</u>	-	-	12	mA
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; <u>Fig. 12</u>	-	1.3	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 13	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 13	0.2	0.3	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic cl	haracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 14	600	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 1 A; dV_{com}/dt = 20 V/s; (snubberless condition); gate open circuit	2.5	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 125 ^{\circ}\text{C}; I_{T(RMS)} = 1 \text{ A};$ $dV_{com}/dt = 10 \text{ V/s}; gate open circuit}$	3.5	-	-	A/ms

25 February 2025

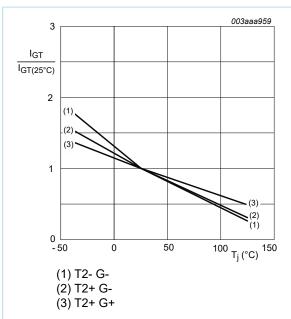


Fig. 9. Normalized gate trigger current as a function of junction temperature

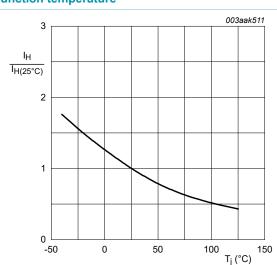


Fig. 11. Normalized holding current as a function of junction temperature

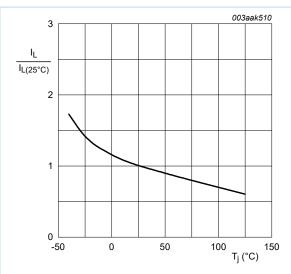
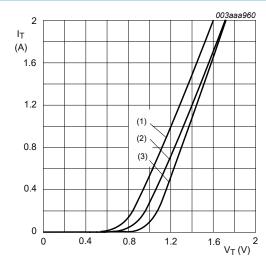


Fig. 10. Normalized latching current as a function of junction temperature



 $\begin{array}{l} \text{V}_{\text{o}} = 1.02 \text{ V}; \text{ R}_{\text{s}} = 0.358 \ \Omega \\ \text{(1)} \text{ T}_{\text{j}} = 125 \ ^{\circ}\text{C}; \text{ typical values} \\ \text{(2)} \text{ T}_{\text{j}} = 125 \ ^{\circ}\text{C}; \text{ maximum values} \\ \text{(3)} \text{ T}_{\text{j}} = 25 \ ^{\circ}\text{C}; \text{ maximum values} \end{array}$

Fig. 12. On-state current as a function of on-state voltage

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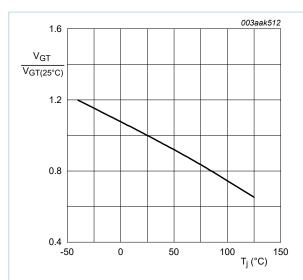


Fig. 13. Normalized gate trigger voltage as a function of junction temperature

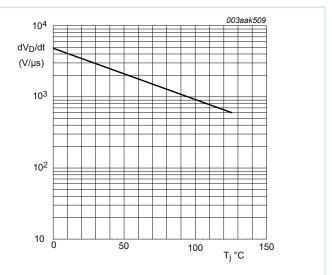


Fig. 14. Critical rate of rise of off-state voltage as a function of junction temperature; minimum values

10. Package outline

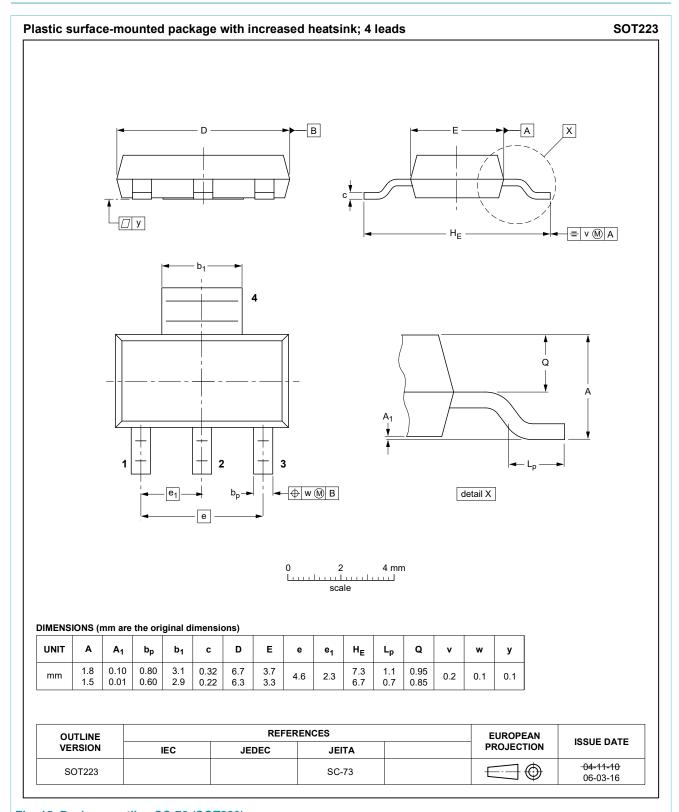
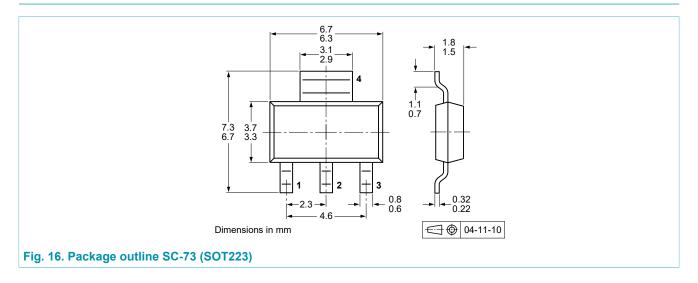
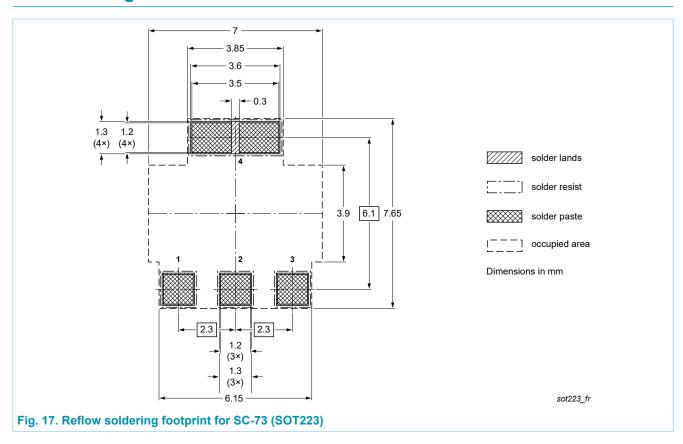


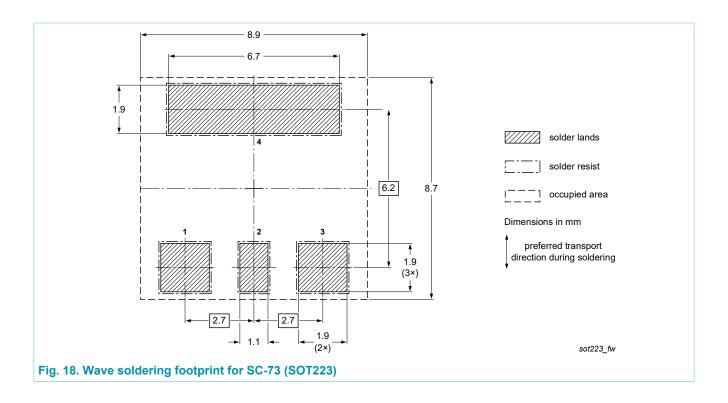
Fig. 15. Package outline SC-73 (SOT223)

11. Package outline (minimized)



12. Soldering





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13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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For more information, please visit: http://www.ween-semi.com
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